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TITLE: ORGANIC THIN-FILM TRANSISTOR  
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## ABSTRACT:

PROBLEM TO BE SOLVED: To provide a thin-film transistor which can be improved in output characteristics by reducing resistance caused between an electrode and a semiconductor layer, and can also be improved in on/off ratio by reducing the leakage current between the source and the drain.

SOLUTION: The thin-film transistor has such a structure that a gate electrode 20, gate insulation layer 30, first semiconductor layer 40, source or drain electrode 50, insulation layer 60, second semiconductor layer 70, and drain or source electrode 80 are formed on a substrate 10. To be more specific, the gate electrode 20 is formed on part of the substrate 10, the

insulation layer 30 is so formed as to cover the gate electrode 20 and the substrate 10, and the first semiconductor layer 40 is formed on the insulation layer 30. The source or drain electrode 50 is formed in part of a region on the first semiconductor layer 40 which corresponds to the gate electrode 20. The insulation layer 60 is formed in a portion on the source or drain electrode 50 which corresponds to a region where the source or drain electrode 50 overlaps the gate electrode 20. The second semiconductor layer 70 is so formed as to cover the semiconductor layer 40 and the insulation layer 60. The drain or source electrode 80 is so formed as to cover part of a region on the second semiconductor layer 70 where the source or drain electrode 50 overlaps the gate electrode 20 which corresponds to the source or drain electrode 50.

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